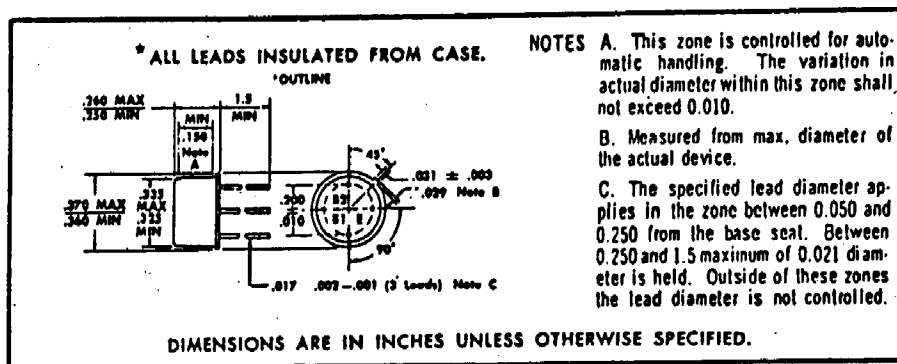


2N1671B Silicon Unijunction Transistors



absolute maximum ratings (25°C)

RMS Power Dissipation	450 mw
RMS Emitter Current	50 ma
Peak Emitter Current	2 amperes
Emitter Reverse Voltage	30 volts
Interbase Voltage	35 volts
Operating Temperature Range	-65°C to +140°C
Storage Temperature Range	-65°C to +150°C

electrical characteristics (25°C)

PARAMETER	SYMBOL	MIN.	MAX.	UNITS
Intrinsic Standoff Ratio ($V_{BB} = 10V$)	η	0.47	0.62	
Interbase Resistance ($V_{BB} = 3V, I_E = 0$)	R_{BB}	4.7	0.1	K Ω
Emitter Saturation Voltage ($V_{BB} = 10V, I_E = 50$ ma)	$V_E(SAT)$		5	volts
Modulated Interbase Current ($V_{BB} = 10V, I_E = 50$ ma)	$I_{BB}(MOD)$	6.8	22	ma
Emitter Reverse Current ($V_{BB} = 30V, I_{B1} = 0$)	I_{E0}		0.2	μA
Peak Point Emitter Current ($V_{BB} = 25V$)	I_P		6	μA
Valley Point Current ($V_{BB} = 20V, R_{BT} = 100\Omega$)	I_V	8		ma
Base-One Peak Pulse Voltage	V_{OB1}	3.0		volts



Quality Semi-Conductors